



256K x 16 Static RAM

Features

- Low voltage range:
 - CY62146V18: 1.75V–1.95V
- Ultra-low active, standby power
- Easy memory expansion with \overline{CE} and \overline{OE} features
- TTL-compatible inputs and outputs
- Automatic power-down when deselected
- CMOS for optimum speed/power

Functional Description

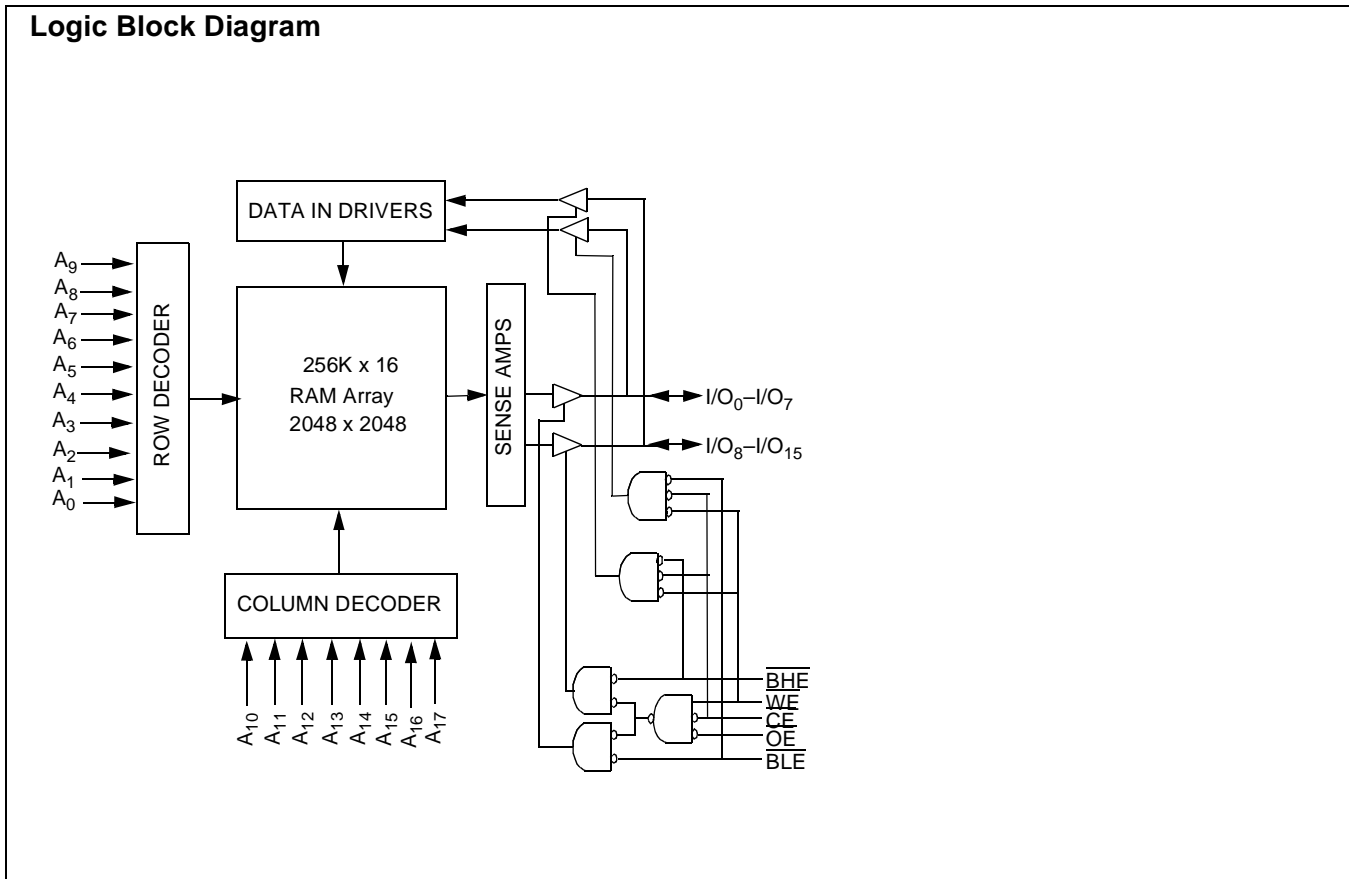
The CY62146V18 is a high-performance CMOS static RAM organized as 262,144 words by 16 bits. These devices feature advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life™ (MoBL™) in portable applications such as cellular telephones. The device also has an automatic power-down feature that significantly reduces power consumption by 99% when addresses are not toggling. The device can also be put into standby mode when deselected (\overline{CE} HIGH). The input/output pins (I/O_0 through

I/O_{15}) are placed in a high-impedance state when deselected (\overline{CE} HIGH), outputs are disabled (\overline{OE} HIGH), \overline{BHE} and \overline{BLE} are disabled (\overline{BHE} , \overline{BLE} HIGH), or during a write operation (\overline{CE} LOW, and \overline{WE} LOW).

Writing to the device is accomplished by taking Chip Enable (\overline{CE}) and Write Enable (\overline{WE}) inputs LOW. If Byte Low Enable (\overline{BLE}) is LOW, then data from I/O pins (I/O_0 through I/O_7), is written into the location specified on the address pins (A_0 through A_{16}). If Byte High Enable (\overline{BHE}) is LOW, then data from I/O pins (I/O_8 through I/O_{15}) is written into the location specified on the address pins (A_0 through A_{17}).

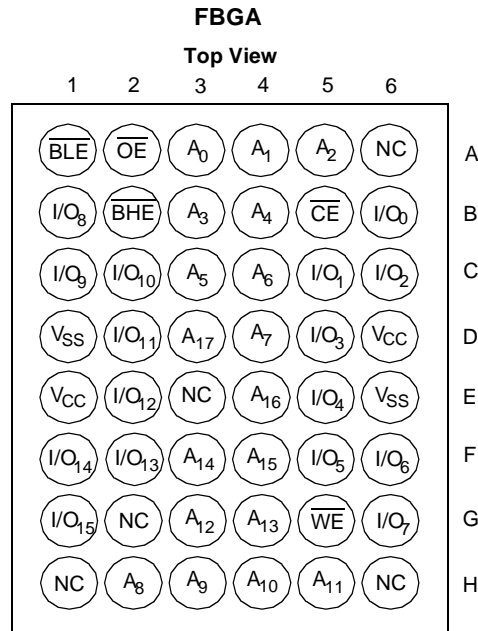
Reading from the device is accomplished by taking Chip Enable (\overline{CE}) and Output Enable (\overline{OE}) LOW while forcing the Write Enable (\overline{WE}) HIGH. If Byte Low Enable (\overline{BLE}) is LOW, then data from the memory location specified by the address pins will appear on I/O_0 to I/O_7 . If Byte High Enable (\overline{BHE}) is LOW, then data from memory will appear on I/O_8 to I/O_{15} . See the truth table at the back of this data sheet for a complete description of read and write modes.

The CY62146V18 is available in 48-Ball FBGA packaging.



MoBL2 and More Battery Life are trademarks of Cypress Semiconductor Corporation.

Pin Configurations



Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature -65°C to +150°C

Ambient Temperature with

Power Applied -55°C to +125°C

Supply Voltage to Ground Potential -0.5V to +2.4V

DC Voltage Applied to Outputs

in High Z State^[1] -0.5V to V_{CC} + 0.5V

DC Input Voltage^[1] -0.5V to V_{CC} + 0.5V

Output Current into Outputs (LOW) 20 mA

Static Discharge Voltage >2001V
(per MIL-STD-883, Method 3015)

Latch-Up Current >200 mA

Operating Range

Device	Range	Ambient Temperature	V _{CC}
CY62146V18	Industrial	-40°C to +85°C	1.75V to 1.95V

Product Portfolio

Product	V _{CC} Range			Power	Power Dissipation (Industrial)			
	V _{CC} (min.)	V _{CC} (typ.) ^[2]	V _{CC} (max.)		Operating (I _{CC})		Standby (I _{SB2})	
					Typ. ^[2]	Maximum	Typ. ^[2]	Maximum
CY62146V18	1.75V	1.80V	1.95V	Std	3 mA	7 mA	20 μA	50 μA

Notes:

1. V_{IL(min.)} = -2.0V for pulse durations less than 20 ns.

2. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = V_{CC(yp.)}, T_A = 25°C.

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions		CY62146V18			Unit
				Min.	Typ. ^[2]	Max.	
V _{OH}	Output HIGH Voltage	I _{OH} = -0.1 mA	V _{CC} = 1.75V	1.5			V
V _{OL}	Output LOW Voltage	I _{OL} = 0.1 mA	V _{CC} = 1.75V			0.2	V
V _{IH}	Input HIGH Voltage		V _{CC} = 1.95V	1.4		V _{CC} + 0.3V	V
V _{IL}	Input LOW Voltage		V _{CC} = 1.75V	-0.5		0.4	V
I _{Ix}	Input Load Current	GND ≤ V _I ≤ V _{CC}		-1	±1	+1	μA
I _{OZ}	Output Leakage Current	GND ≤ V _O ≤ V _{CC} , Output Disabled		-1	+1	+1	μA
I _{CC}	V _{CC} Operating Supply Current	I _{OUT} = 0 mA, f = f _{MAX} = 1/t _{RC} , CMOS Levels	V _{CC} = 1.95V		7	15	mA
		I _{OUT} = 0 mA, f = 1 MHz, CMOS Levels			1	2	mA
I _{SB1}	Automatic CE Power-Down Current—CMOS Inputs	$\overline{CE} \geq V_{CC} - 0.3V$, $V_{IN} \geq V_{CC} - 0.3V$ or $V_{IN} \leq 0.3V$, f = f _{MAX}				100	μA
I _{SB2}	Automatic CE Power-Down Current—CMOS Inputs	$\overline{CE} \geq V_{CC} - 0.3V$ $V_{IN} \geq V_{CC} - 0.3V$ or $V_{IN} \leq 0.3V$, f = 0	V _{CC} = 1.95V	Std.	20	50	μA

Capacitance^[3]

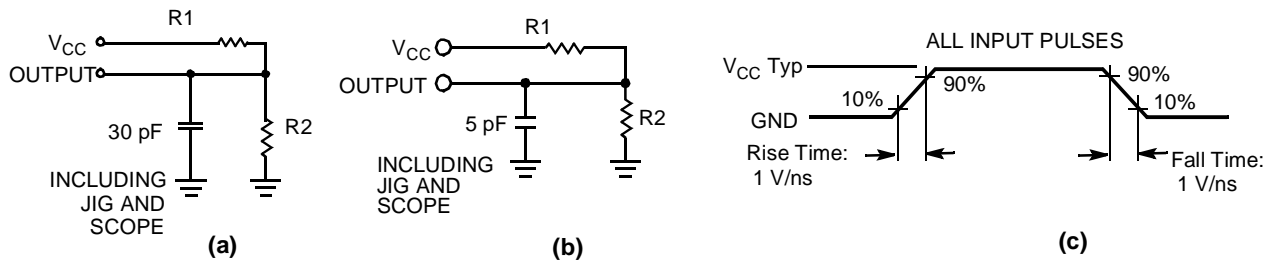
Parameter	Description	Test Conditions	Max.	Unit
C _{IN}	Input Capacitance	T _A = 25°C, f = 1 MHz, V _{CC} = V _{CC} (typ.)	6	pF
C _{OUT}	Output Capacitance		8	pF

Thermal Resistance

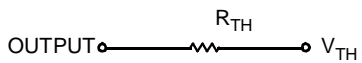
Description	Test Conditions	Symbol	BGA	Unit
Thermal Resistance (Junction to Ambient) ^[3]	Still Air, soldered on a 4.25 x 1.125 inch, 4-layer printed circuit board	Θ _{JA}	55	°C/W
Thermal Resistance (Junction to Case) ^[3]		Θ _{JC}	16	°C/W

Note:

- Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms


Equivalent to: THÉVENIN EQUIVALENT



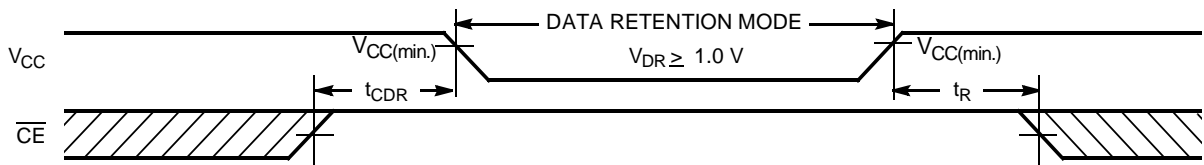
Parameters	1.8V	Unit
R1	15294	Ohms
R2	11300	Ohms
R_{TH}	6500	Ohms
V_{TH}	0.85V	Volts

Data Retention Characteristics (Over the Operating Range)

Parameter	Description	Conditions	Min.	Typ. ^[2]	Max.	Unit
V_{DR}	V_{CC} for Data Retention		1.0		1.95	V
I_{CCDR}	Data Retention Current	$V_{CC} = 1.0V$ $CE \geq V_{CC} - 0.3V$, $V_{IN} \geq V_{CC} - 0.3V$ or $V_{IN} \leq 0.3V$ No input may exceed $V_{CC} + 0.3V$	Std	10	25	μA
$t_{CDR}^{[3]}$	Chip Deselect to Data Retention Time		0			ns
$t_R^{[4]}$	Operation Recovery Time		85			ns

Note:

4. Full Device AC operation requires linear V_{CC} ramp from V_{DR} to $V_{CC(min.)} \geq 10\ \mu s$ or stable $V_{CC(min.)} \geq 10\ \mu s$.

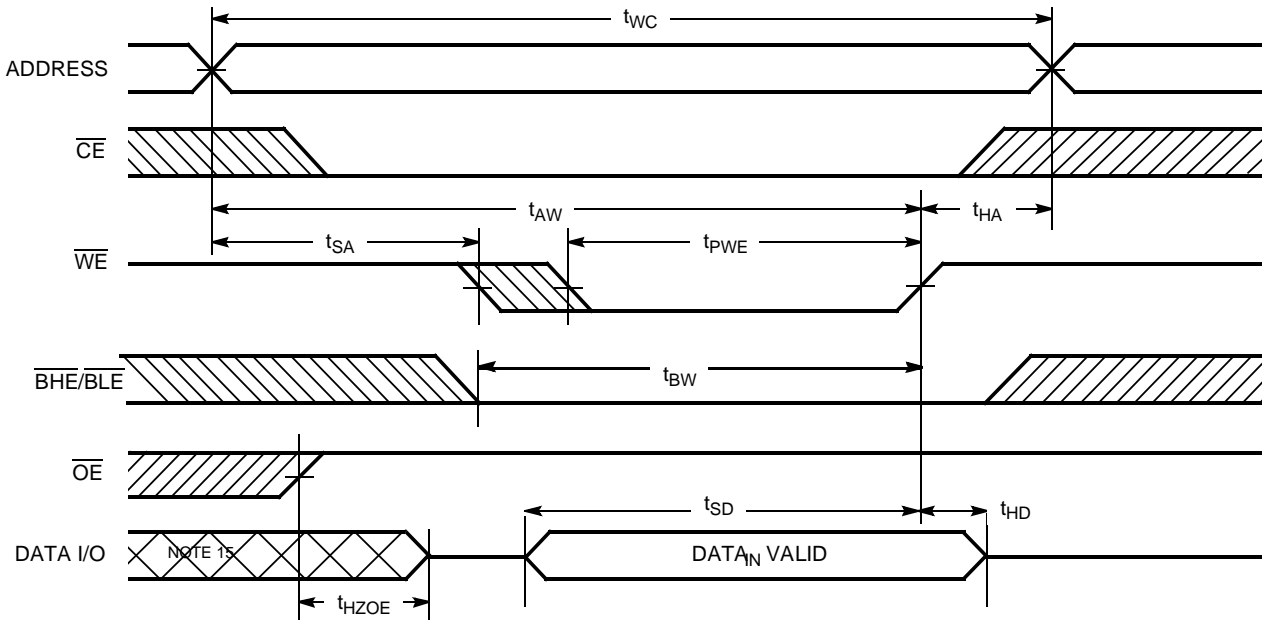
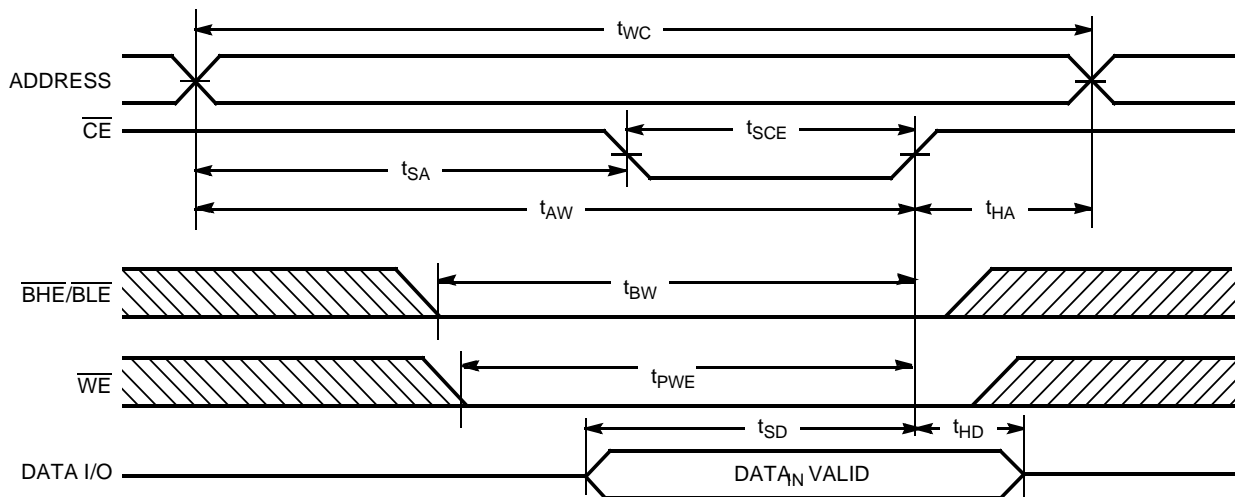
Data Retention Waveform


Switching Characteristics Over the Operating Range^[5]

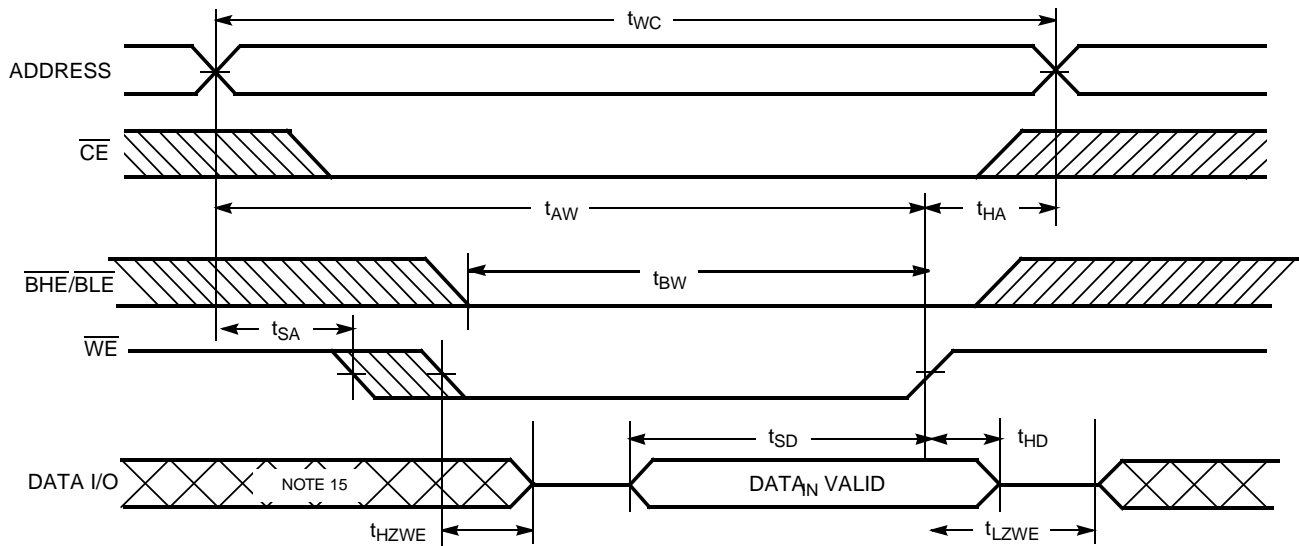
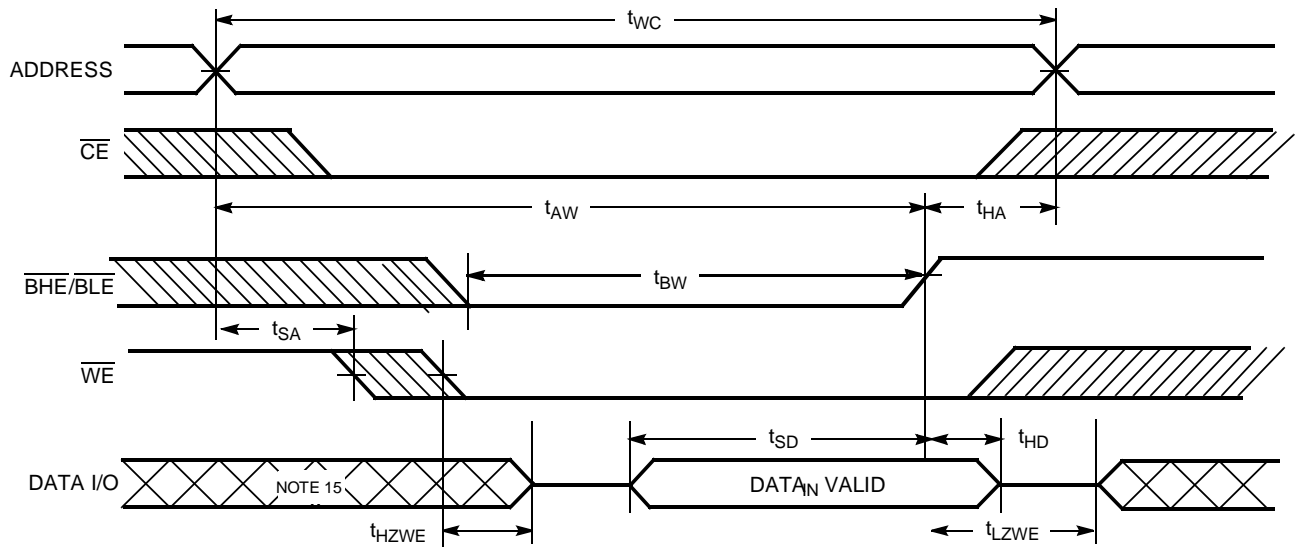
Parameter	Description	85 ns		Unit
		Min.	Max.	
READ CYCLE				
t _{RC}	Read Cycle Time	85		ns
t _{AA}	Address to Data Valid		85	ns
t _{OHA}	Data Hold from Address Change	10		ns
t _{ACE}	\overline{CE} LOW to Data Valid		85	ns
t _{DOE}	\overline{OE} LOW to Data Valid		45	ns
t _{LZOE}	\overline{OE} LOW to Low Z ^[6, 7]	5		ns
t _{HZOE}	\overline{OE} HIGH to High Z ^[7]		25	ns
t _{LZCE}	\overline{CE} LOW to Low Z ^[6]	10		ns
t _{HZCE}	\overline{CE} HIGH to High Z ^[6, 7]		25	ns
t _{PU}	\overline{CE} LOW to Power-Up	0		ns
t _{PD}	\overline{CE} HIGH to Power-Down		85	ns
t _{DBE}	\overline{BHE} / \overline{BLE} LOW to Data Valid		45	ns
t _{LZBE}	\overline{BHE} / \overline{BLE} LOW to Low Z	5		ns
t _{HZBE}	\overline{BHE} / \overline{BLE} HIGH to High Z		25	ns
WRITE CYCLE^[8, 9]				
t _{WC}	Write Cycle Time	85		ns
t _{SCE}	\overline{CE} LOW to Write End	75		ns
t _{AW}	Address Set-Up to Write End	75		ns
t _{HA}	Address Hold from Write End	0		ns
t _{SA}	Address Set-Up to Write Start	0		ns
t _{PWE}	\overline{WE} Pulse Width	65		ns
t _{BW}	\overline{BHE} / \overline{BLE} Pulse Width	75		ns
t _{SD}	Data Set-Up to Write End	45		ns
t _{HD}	Data Hold from Write End	0		ns
t _{HZWE}	\overline{WE} LOW to High Z ^[6, 7]		35	ns
t _{LZWE}	\overline{WE} HIGH to Low Z ^[6]	10		ns

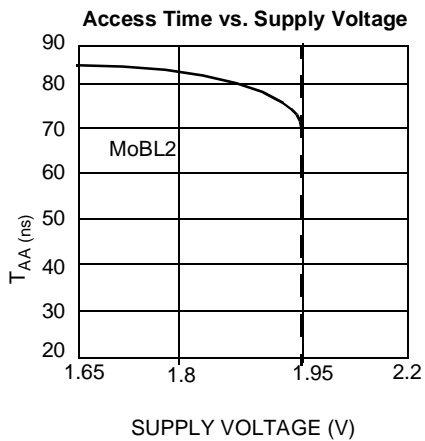
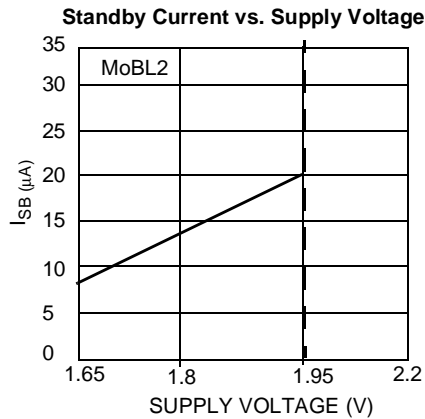
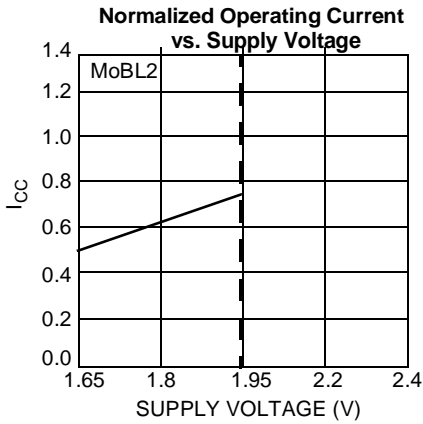
Notes:

5. Test conditions assume signal transition time of 5 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to V_{CC(typ.)}, and output loading of the specified I_{OL}/I_{OH} and 30 pF load capacitance.
6. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
7. t_{HZOE}, t_{HZCE}, and t_{HZWE} are specified with C_L = 5 pF as in part (b) of AC Test Loads. Transition is measured ±500 mV from steady-state voltage.
8. The internal write time of the memory is defined by the overlap of \overline{CE} LOW and \overline{WE} LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.
9. The minimum write cycle time for Write Cycle #3 (\overline{WE} controlled, \overline{OE} LOW) is the sum of t_{HZWE} and t_{SD}.

Switching Waveforms (continued)
Write Cycle No. 1 (\overline{WE} Controlled) ^[8, 13, 14]

Write Cycle No. 2 (\overline{CE} Controlled) ^[8, 13, 14]

Notes:

13. Data I/O is high-impedance if $\overline{OE} = V_{IH}$.
14. If \overline{CE} goes HIGH simultaneously with \overline{WE} HIGH, the output remains in a high-impedance state.
15. During this period, the I/Os are in output state and input signals should not be applied.

Switching Waveforms (continued)
Write Cycle No. 3 (\overline{WE} Controlled, \overline{OE} LOW)^[9, 14]

Write Cycle No. 4 ($\overline{BHE}/\overline{BLE}$ Controlled, \overline{OE} LOW)^[15]


Typical DC and AC Characteristics

Truth Table

CE	WE	OE	BHE	BLE	Inputs/Outputs	Mode	Power
H	X	X	X	X	High Z	Deselect/Power-Down	Standby (I_{SB})
L	H	L	L	L	Data Out (I/O ₀ –I/O ₁₅)	Read	Active (I_{CC})
L	H	L	H	L	Data Out (I/O ₀ –I/O ₇); I/O ₈ –I/O ₁₅ in High Z	Read	Active (I_{CC})
L	H	L	L	H	Data Out (I/O ₈ –I/O ₁₅); I/O ₀ –I/O ₇ in High Z	Read	Active (I_{CC})
L	H	L	H	H	High Z	Output Disabled	Active (I_{CC})
L	H	H	X	X	High Z	Output Disabled	Active (I_{CC})
L	L	X	L	L	Data In (I/O ₀ –I/O ₁₅)	Write	Active (I_{CC})
L	L	X	H	L	Data In (I/O ₀ –I/O ₇); I/O ₈ –I/O ₁₅ in High Z	Write	Active (I_{CC})
L	L	X	L	H	Data In (I/O ₈ –I/O ₁₅); I/O ₀ –I/O ₇ in High Z	Write	Active (I_{CC})
L	L	X	H	H	High Z	Output Disabled	Active (I_{CC})

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
85	CY62146V18 -85BAI	BA49	48-Ball Fine Pitch BGA	Industrial

Document #: 38-01046-**

Package Diagrams
48-Ball (7.00 mm x 8.5 mm x 1.10 mm) Fine Pitch BGA BA49
